

TRANSISTOR SWITCH FOR HIGH FREQUENCY AND HIGH POWER
APPLICATIONS

ABSTRACT OF THE DISCLOSURE

[0023] A transistor switch for a system operating at high frequencies is provided. The transistor switch comprises a graded channel region between a source region and a drain region, the graded channel region configured for providing a low resistance to mobile negative charge carriers moving from the source region to the drain region, wherein the graded channel comprises at least two doping levels.